

Please replace the paragraph beginning on page 27, line 15, with the following new paragraph:

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FIG. 62 is a perspective view showing a contact portion of the MOSFET according to the embodiments of the present invention.

Please replace the paragraph beginning on page 27, line 18, with the following new paragraph:

FIG. 63A is a plan view showing the contact portion of the MOSFET according to the embodiments of the present invention; FIG. 63B is a side view as seen from a direction of an arrow B shown in FIG. 63A; and FIG. 63C is a side view as seen from the direction of an arrow C shown in FIG. 63A.

IN THE CLAIMS:

Please cancel claim 22 without prejudice or disclaimer of the subject matter thereof and amend claim 1, as follows:

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C1
B6
1. (Amended) A semiconductor device comprising:
a convex semiconductor layer provided on a semiconductor substrate;
a source region and a drain region provided in the convex semiconductor layer;
and
a gate electrode having a side-wall gate portion provided over a side surface of the convex semiconductor layer, in an insulated state with respect to the convex semiconductor layer, the gate electrode applying an electric field effect to a channel

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